



Docket No.: M4065.0457/P457-B  
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:  
Kristy A. Campbell

Application No.: 10/603,670

Group Art Unit: 2826

Filed: June 26, 2003

Examiner: Johannes P. Mondt

For: STOICHIOMETRY FOR  
CHALCOGENIDE GLASSES USEFUL  
FOR MEMORY DEVICES AND  
METHOD OF FORMATION

INFORMATION DISCLOSURE STATEMENT (IDS)

Commissioner for Patents  
Washington, DC 20231

Dear Sir:

Pursuant to 37 C.F.R. § 1.56, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO/SB/08. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

Those patent(s) or publication(s) which are marked with an asterisk (\*) in the attached form PTO/SB/08 are not supplied because they were previously cited by or submitted to the Office in a prior application no. 09/941,544, filed August 30, 2001 and relied upon in this application for an earlier filing date under 35 U.S.C. 120.

A concise explanation of relevance of the items listed on form PTO/SB/08 is:

[x] not given

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While the information and references disclosed in this Information Disclosure Statement may be “material” pursuant to 37 C.F.R. § 1.56, it is not intended to constitute an admission that any patent, publication or other information referred to therein is “prior art” for this invention unless specifically designated as such.

In accordance with 37 C.F.R. § 1.97(g), the filing of this Information Disclosure Statement shall not be construed to mean that a search has been made or that no other material information as defined in 37 C.F.R. § 1.56(a) exists. It is submitted that the Information Disclosure Statement is in compliance with 37 C.F.R. § 1.98 and the Examiner is respectfully requested to consider the listed references.

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Application No.: 10/603,670

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Dated: October 12, 2004

Respectfully submitted,

By 

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Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Sheet 1 of 10

**Complete if Known**

Application Number	10/603,670
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First Named Inventor	Kristy A. Campbell
Art Unit	2826
Examiner Name	Johannes P. Mondt
Attorney Docket Number	M4065.0457/P457-B

**U.S. PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
	AA	6,388,324	05/14/2002	Kozicki et al.*	
	AB	US 2002/0000666	01/03/2002	Kozicki et al.*	
	AC	5,500,532	03/19/1996	Kozicki et al.*	
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	AF	5,789,277	08/04/1998	Zahorik et al.*	
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**FOREIGN PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)				
	BA	WO 02/21542	03/14/2002	Kozicki et al.*		
	BB	WO 00/48196	08/17/2000	Kozicki et al.*		
	BC	WO 97/48032	12/18/1997	Kozicki et al.*		
	BD	WO 99/28914	06/10/1999	Kozicki et al.*		

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<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See attached Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

Substitute for form 1449B/PTO				<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)				Application Number	10/603,670
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Sheet	2	of	10	Attorney Docket Number	M4065.0457/P457-B

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
	CA	Abdel-Ali, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge <sub>5</sub> As <sub>38</sub> Te <sub>57</sub> chalcogenide glass, Vacuum 59 (2000) 845-853. *	
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Substitute for form 1449B/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i>				<b>Complete If Known</b>	
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				Group Art Unit	2826
				Examiner Name	Johannes P. Mondt
Sheet	3	of	10	Attorney Docket Number	M4065.0457/P457-B

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	CU1	El Bouchairi, B.; Bernede, J.C.; Burgaud, P., Properties of Ag <sub>2</sub> -xSe <sub>1+x/n</sub> -Si diodes, Thin Solid Films 110 (1983) 107-113. *	
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	CD2	Fadel, M., Switching phenomenon in evaporated Se-Ge-As thin films of amorphous chalcogenide glass, Vacuum 44 (1993) 851-855. *	
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	CR2	Haifz, M.M.; Ibrahim, M.M.; Dongol, M.; Hammad, F.H., Effect of composition on the structure and electrical properties of As-Se-Cu glasses, J. Appl. Phys. 54 (1983) 1950-1954. *	
	CS2	Hajto, J.; Rose, M.J.; Osborne, I.S.; Snell, A.J.; Le Comber, P.G.; Owen, A.E., Quantization effects in metal/a-Si:H/metal devices, Int. J. Electronics 73 (1992) 911-913. *	
	CT2	Hajto, J.; Hu, J.; Snell, A.J.; Turvey, K.; Rose, M., DC and AC measurements on metal/a-Si:H/metal room temperature quantised resistance devices, J. Non-Cryst. Solids 266-269 (2000) 1058-1061. *	
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Sheet	6	of	10	Attorney Docket Number	M4065.0457/P457-B

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Sheet	7	of	10	Attorney Docket Number	M4065.0457/P457-B

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Sheet	10	of	10		